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Metrology, Inspection, and Process Control for Microlithography XXX

**Martha I. Sanchez
Vladimir A. Ukraintsev**
Editors

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Contents

Part One

xi	<i>Authors</i>
xix	<i>Conference Committee</i>
xxiii	<i>Introduction</i>

OPTICAL METROLOGY I

9778 04	Scatterometry modeling for gratings with roughness and irregularities [9778-3]
9778 05	Modeling ellipsometric measurement of novel 3D structures with RCWA and FEM simulations [9778-4]
9778 06	Improving OCD time to solution using Signal Response Metrology [9778-5]
9778 07	Innovative scatterometry approach for self-aligned quadruple patterning (SAQP) process control [9778-7]
9778 08	Lensless hyperspectral spectromicroscopy with a tabletop extreme-ultraviolet source [9778-15]

SEM I: MODELING AND SIMULATION

9778 09	Virtual rough samples to test 3D nanometer-scale scanning electron microscopy stereo photogrammetry [9778-8]
9778 0A	Improvements to the analytical linescan model for SEM metrology [9778-9]
9778 0B	Gaining insight into effective metrology height through the use of a compact CDSEM model for lithography simulation [9778-10]
9778 0C	Electric fields in Scanning Electron Microscopy simulations [9778-11]
9778 0D	GPU accelerated Monte-Carlo simulation of SEM images for metrology [9778-12]

NEW HORIZONS

9778 0E	HVM metrology challenges towards the 5nm node (Invited Paper) [9778-13]
9778 0F	Multiple beam ptychography [9778-14]

- 9778 OG Measurement of asymmetric side wall angles by coherent scanning Fourier scatterometry [9778-16]
- 9778 OH Non-contact distance measurement and profilometry using thermal near-field radiation towards a high resolution inspection and metrology solution [9778-17]
- 9778 OI Reliable characterization of materials and nanostructured systems < 50 nm using coherent EUV beams [9778-18]
- 9778 OJ Spectroscopic imaging of buried layers in 2+1D via tabletop ptychography with high-harmonic EUV illumination [9778-6]

X-RAY METHODS

- 9778 OL Characterization of cross-sectional profile of resist L/S and hole pattern using CD-SAXS [9778-20]
- 9778 OM Hybrid enabled thin film metrology using XPS and optical [9778-21]
- 9778 ON XPS-XRF hybrid metrology enabling FDSOI process [9778-22]

INSPECTION

- 9778 OO Study of design-based e-beam defect inspection for hotspot detection and process window characterization on 10nm logic device [9778-24]
- 9778 OP Electromagnetic field modeling for defect detection in 7 nm node patterned wafers [9778-25]
- 9778 OQ Detection of metallic buried void by effective density contrast mode [9778-26]
- 9778 OR Topological study of nanomaterials using surface-enhanced ellipsometric contrast microscopy (SEEC) [9778-105]

PROCESS CONTROL

- 9778 OT Focus control enhancement and on-product focus response analysis methodology [9778-28]
- 9778 OU Analysis of wafer heating in 14nm DUV layers [9778-29]
- 9778 OV Line width roughness accuracy analysis during pattern transfer in self-aligned quadruple patterning process [9778-30]
- 9778 OW Design-based metrology: beyond CD/EPE metrics to evaluate printability performance (Invited Paper) [9778-31]
- 9778 OX A new approach to process control using Instability Index [9778-32]

OPTICAL METROLOGY II

- 9778 0Y **Enabling quantitative optical imaging for in-die-capable critical dimension targets (Invited Paper)** [9778-33]
- 9778 0Z **Optical metrology solutions for 10nm films process control challenges** [9778-34]
- 9778 10 **Advanced in-line optical metrology of sub-10nm structures for gate all around devices (GAA)** [9778-35]
- 9778 11 **Optimizing noise for defect analysis with through-focus scanning optical microscopy** [9778-36]
- 9778 12 **Monitoring of ion implantation in microelectronics production environment using multi-channel reflectometry** [9778-37]
- 9778 13 **Advanced in-line metrology strategy for self-aligned quadruple patterning** [9778-90]

SEM II

- 9778 14 **Process monitor of 3D-device features by using FIB and CD-SEM** [9778-38]
- 9778 15 **Free surface BCP self-assembly process characterization with CDSEM** [9778-39]
- 9778 16 **Advanced CD-SEM metrology for qualification of DSA patterns using coordinated line epitaxy (COOL) process** [9778-40]
- 9778 17 **Identification of multilayer structures using secondary electron yield curves: effect of native oxide films on EUV-patterned mask inspection** [9778-41]

AFM

- 9778 18 **Simultaneous AFM nano-patterning and imaging for photomask repair** [9778-42]
- 9778 1A **Device level 3D characterization using PeakForce AFM** [9778-44]
- 9778 1B **Large dynamic range Atomic Force Microscope for overlay improvements** [9778-45]

OVERLAY: METROLOGY TARGET DESIGN AND OPTIMIZATION

- 9778 1E **In-depth analysis of sampling optimization methods** [9778-48]
- 9778 1F **Device overlay method for high volume manufacturing** [9778-49]
- 9778 1H **Accuracy in optical overlay metrology** [9778-51]
- 9778 1I **A study of swing-curve physics in diffraction-based overlay** [9778-52]

- 9778 1J Enhancement of intrafield overlay using a design based metrology system [9778-53]

OVERLAY OPTIMIZATION: JOINT SESSION WITH CONFERENCES 9778 AND 9780

- 9778 1K Assessments of image-based and scatterometry-based overlay targets [9778-55]
- 9778 1L Lithography aware overlay metrology target design method [9778-56]
- 9778 1M Root cause analysis of overlay metrology excursions with scatterometry overlay technology (SCOL) [9778-117]

MASK INSPECTION

- 9778 1N Material analysis techniques used to drive down in-situ mask contamination sources [9778-57]
- 9778 1O Scanning scattering contrast microscopy for actinic EUV mask inspection [9778-58]

DESIGN INTERACTION WITH METROLOGY: JOINT SESSION WITH CONFERENCES 9778 AND 9781

- 9778 1Q Modeling metrology for calibration of OPC models [9778-61]
- 9778 1R Process window limiting hot spot monitoring for high-volume manufacturing [9778-63]
- 9778 1S OPC optimization techniques for enabling the reduction of mismatch between overlay metrology and the device pattern cell [9778-137]

Part Two

LATE BREAKING NEWS

- 9778 1T 3D-profile measurement of advanced semiconductor features by reference metrology [9778-64]
- 9778 1U Resist 3D model based OPC for 28nm metal process window enlargement [9778-65]
- 9778 1V Patterning and imaging with electrons: assessing multi-beam SEM for e-beam structured CMOS samples [9778-66]
- 9778 1W Scatterometry-based metrology for SAQP pitch walking using virtual reference [9778-134]
- 9778 1X Challenges in LER/CDU metrology in DSA: placement error and cross-line correlations [9778-143]
- 9778 1Y Holistic overlay control for multi-patterning process layers at the 10nm and 7nm nodes [9778-141]

POSTER SESSION

- 9778 1Z **Simulation of shotnoise induced side-wall roughness in electron lithography** [9778-67]
- 9778 20 **Scatterometry-based process control for nanoimprint lithography** [9778-68]
- 9778 21 **Oblique incidence scatterometry for 2D/3D isolation mounts with RCWA and PML** [9778-69]
- 9778 22 **Comparison of left and right side line edge roughness in lithography** [9778-70]
- 9778 23 **Generalized measurement configuration optimization for accurate reconstruction of periodic nanostructures using optical scatterometry** [9778-71]
- 9778 24 **Hybrid overlay metrology for high order correction by using CDSEM** [9778-72]
- 9778 25 **Application of overlay modeling and control with Zernike polynomials in an HVM environment** [9778-73]
- 9778 26 **Highly sensitive focus monitoring technique based on illumination and target co-optimization** [9778-74]
- 9778 27 **Scan direction induced charging dynamics and the application for detection of gate to S/D shorts in logic devices** [9778-75]
- 9778 28 **Image-based overlay (IBO) target segment design on self-aligned patterning process** [9778-77]
- 9778 29 **Improving focus performance at litho using diffraction-based focus metrology, novel calibration methods, interface, and control loop** [9778-78]
- 9778 2A **A novel mask structure for measuring the defocus of scanner** [9778-79]
- 9778 2B **Spacer multi-patterning control strategy with optical CD metrology on device structures** [9778-80]
- 9778 2C **Study on overlay AEI-ADI shift on contact layer of advanced technology node** [9778-81]
- 9778 2D **Design guided data analysis for summarizing systematic pattern defects and process window** [9778-83]
- 9778 2E **Mixed-mode, high-order multi-patterning control strategy with small-spot, optical CD metrology on device structures** [9778-84]
- 9778 2G **Overlay optimization for 1x node technology and beyond via rule based sparse sampling** [9778-86]
- 9778 2J **Overlay metrology performance prediction fidelity: the factors enabling a successful target design cycle** [9778-91]
- 9778 2K **Advanced overlay: sampling and modeling for optimized run-to-run control** [9778-92]
- 9778 2L **Probe microscopy for metrology of next generation devices** [9778-93]

- 9778 2M Improving scanner wafer alignment performance by target optimization [9778-94]
- 9778 2N New approaches in diffraction based optical metrology [9778-95]
- 9778 2O Process window optimizer for pattern based defect prediction on 28nm metal layer [9778-96]
- 9778 2P Studying post-etching silicon crystal defects on 300mm wafer by automatic defect review AFM [9778-97]
- 9778 2Q Comparison study of diffraction based overlay and image based overlay measurements on programmed overlay errors [9778-98]
- 9778 2R Metrology target design (MTD) solution for diagonally orientated DRAM layer [9778-99]
- 9778 2S Electrostatic risks to reticles and damage prevention methodology [9778-100]
- 9778 2T Investigation on the relationship between CD and CDU in memory devices [9778-101]
- 9778 2U Triple AIM evaluation and application in advanced node [9778-102]
- 9778 2V Applications of on-product diffraction-based focus metrology in logic high volume manufacturing [9778-103]
- 9778 2W Study of correlation between overlay and displacement measured by Coherent Gradient Sensing (CGS) interferometry [9778-104]
- 9778 2X Controlling bridging and pinching with pixel-based mask for inverse lithography [9778-106]
- 9778 2Y An evaluation of edge roll off on 28nm FDSOI (fully depleted silicon on insulator) product [9778-108]
- 9778 2Z EUV blank defect and particle inspection with high throughput immersion AFM with 1nm 3D resolution [9778-109]
- 9778 31 Process tool monitoring and matching using interferometry technique [9778-111]
- 9778 32 Reducing overlay sampling for APC-based correction per exposure by replacing measured data with computational prediction [9778-112]
- 9778 34 Automated klarf-based defect inspection by electron-beam inspection tool: a novel approach to inline monitoring and/or process change validation [9778-114]
- 9778 35 Sub 20nm particle inspection on EUV mask blanks [9778-115]
- 9778 36 Next generation of decision making software for nanopatterns characterization: application to semiconductor industry [9778-116]
- 9778 38 Scanner baseliner monitoring and control in high volume manufacturing [9778-119]
- 9778 39 Method for fast computation of angular light scattering spectra from 2D periodic arrays [9778-120]

- 9778 3A **Sensitivity study and parameter optimization of OCD tool for 14nm finFET process [9778-121]**
- 9778 3B **Metrology target design simulations for accurate and robust scatterometry overlay measurements [9778-122]**
- 9778 3C **An ultrasensitive bio-surrogate for nanoporous filter membrane performance metrology directed towards contamination control in microlithography applications [9778-123]**
- 9778 3D **Co-optimization of RegC and TWINSKAN corrections to improve the intra-field on-product overlay performance [9778-124]**
- 9778 3E **Within-wafer CD variation induced by wafer shape [9778-125]**
- 9778 3F **Process window and defect monitoring using high-throughput e-beam inspection guided by computational hot spot detection [9778-126]**
- 9778 3G **Holistic, model-based optimization of edge leveling as an enabler for lithographic focus control: application to a memory use case [9778-128]**
- 9778 3H **The effect of materials selection on metals reduction in propylene glycol methyl ether acetate, PGMEA [9778-129]**
- 9778 3I **Detection of electrical defects with SEMVision in semiconductor production mode manufacturing [9778-130]**
- 9778 3J **Recipe creation for automated defect classification with a 450mm surface scanning inspection system based on the bidirectional reflectance distribution function of native defects [9778-132]**
- 9778 3K **Focus measurement using SEM image analysis of circuit pattern [9778-135]**
- 9778 3L **Surface profile measurement of highly reflective silicon wafer using wavelength tuning interferometer [9778-136]**
- 9778 3M **Automatic pattern localization across layout database and photolithography mask [9778-138]**
- 9778 3N **Prediction of ppm level electrical failure by using physical variation analysis [9778-139]**
- 9778 3O **Excursion detection using leveling data [9778-140]**
- 9778 3Q **Net tracing and classification analysis on E-beam die-to-database inspection [9778-146]**
- 9778 3S **A novel method to quantify the complex mask patterns [9778-60]**
- 9778 3V **A study of lateral roughness evaluation through critical-dimension small angle x-ray scattering (CD-SAXS) [9778-144]**
- 9778 3X **Proposed approach to drive wafer topography for advanced lithography [9778-54]**

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abe, Hideaki, 20	Brinster, Irina, 1F
Abramovitz, Yaniv, 2R	Brown, Justin, 3J
Ache, Oliver, 3M	Bruls, Richard J., 1N
Adam, Ido, 1H	Buhl, Stefan, 1E
Adam, Kostas, 1Q	Bunday, Benjamin D., 0A, 0E, 2L
Adam, Omer, 1Y	Burger, Sven, 39
Adams, Daniel E., 08, 0F, 0J	Bussink, Peter, 35
Adan, Ofer, 15	Byun, Jin-Moo, 2B, 2E
Adel, Michael E., 1L, 1M, 2J, 2R, 3B	Cadoux, C., 3V
Ahmad, Farhan, 3C	Cai, Na, 34, 3Q
Ahn, Ki Cheol, 1M	Callan, Neal, 1R
Altamirano Sanchez, Efrain, 07, 0V	Camp, Janay, 0Z, 1M
Alumot, Dror, 1H	Cardinal, Tom, 13
An, Kevin, 1I	Cekli, Hakki Ergun, 3D
Anberg, Doug, 2W, 31	Cepler, Aron, 10, 13, 1W
Anunciado, Roy, 1R	Chai, Yvon, 2B, 2E
Arat, K. T., 0C	Chao, Robin, 10, 13
Argoud, Maxime, 15	Chao, Weilun, 0I
Arnold, John, 22	Charley, Anne-Laure, 07
Asano, Masafumi, 20	Chen, Albert, 1Y
Ashwal, Eltsafon, 1H	Chen, Bryan, 1H
Attota, Ravikiran, 11	Chen, Charlie, 2U
Aung, Nyan Lynn, 0U, 2G, 2K, 2Q, 38	Chen, Chia-Hung, 2R
Azuma, Tsukasa, 16	Chen, Chu-en, 3N
Barnes, B. M., 0Y	Chen, Hsiang-Lin, 3S
Bastard, David, 2L	Chen, Huiping, 3A
Baudempretz, Bart, 24	Chen, K. C., 3E
Bedford, Eilidh, 3C	Chen, K. H., 29
Beems, Marcel, 1B	Chen, Y. L., 29
Beique, Genevieve, 22	Chen, Yaqiong, 0Q
Beisser, Eric, 3M	Chen, Yen-Jen, 0T, 2G
Belen, Jun, 2M	Chen, Yulu, 22
Bellmann, Enrico, 1E, 3O	Chen, Zhijin, 2D, 3Q
Bello, Abner F., 0M, 0N	Cheng, Harvey, 2R
Ben-Dov, Guy, 2J, 3B	Cheng, Shiqiu, 3A
Bevis, Charles, 0F, 0J	Chin, Jo-Lan, 2R
Beyer, Dirk, 3D	Cho, Sang-Joon, 2P
Bhattacharyya, Kaustuve, 1I, 1Y, 29	Cho, Winston, 1M
Bijster, Roy, 0H	Choi, DongSub, 1F, 1L, 3B
Bischoff, Joerg, 04	Chou, Kuo-Yao, 2R
Blancquaert, Y., 3V	Chuang, Shu-Chuan, 3S
Boeckx, C., 36	Chung, Woong Jae, 0U, 2G, 2K, 2Q, 38
Bolten, J., 0C	Claveau, Guillaume, 15
Bolton, David, 2V	Cohen, Avi, 3D
Bouche, Eric, 2W, 31	Cohen, Oded, 07, 10
Bozdog, Cornel, 0M, 10, 13, 1W	Colburn, Matthew, 22
Brault, Frederic, 3M	Constantoudis, Vassilios, 0V, 1X
Breton, Mary, 13	Cramer, Hugo, 2B, 2E, 2N
Bringoltz, Barak, 1H	Crowcombe, Will, 1B

Dasari, Prasad, 0M, 1W
 Davoudzadeh, Nima, 0P
 De La Pena, Abraham, 13
 DeLeeuw, Yaron, 1H
 Dellemann, Gregor, 1V
 Demarest, James, 13
 Demirer, Onur Nihat, 2K
 den Boef, Arie, 1B, 1I
 Deng, Guogui, 2C
 Deng, Yunfei, 1Q
 Depre, L., 1U, 2O
 Dervillé, A., 36
 Di Lorenzo, Paolo, 0O
 Diebold, Alain C., 05
 Dillen, Harm, 1N
 Dmitriev, Vladimir, 3D
 Dong, Lisong, 2A
 Dror, Chen, 2J, 2R
 Duivenvoorde, Tom, 1B
 Ebersbach, Peter, 12
 Ebert, M., 2N
 Ekinci, Y., 1O
 El Kodadi, Mohamed, 3B
 Elich, Frank, 1Y
 Entezarian, Majid, 3H
 Erley, Georg, 3O
 Escalante Marun, Maryana, 29
 Etzioni, Yoav, 1W
 Fang, Chao, 0B
 Fang, Fang, 06, 0Z, 1W
 Fang, Wei, 0O, 3F
 Fanton, P., 1U, 2O
 Feinstein, Adam, 1A
 Feler, Yoel, 1H
 Felix, Nelson, 10, 13, 1K, 22
 Foucher, J., 36
 Foussadier, F., 1U
 Frazer, Travis, 0I
 Frenner, K., 0G
 Freychet, G., 3V
 Fritz, Erik, 1B, 35
 Furthner, Francois, 29
 Gallagher, Emily, 3D
 Gao, Haiyong, 0U, 2G, 2K, 2Q, 38
 Gao, Kewen, 0Q, 34
 Gao, Weihong, 34, 3Q
 Gao, Xindong, 1H
 Garbowski, Tomasz, 1V
 Garcia-Medina, Miguel, 2K
 Gardin, C., 1U
 Gardiola, C., 1U
 Gardner, Dennis F., 08, 0F, 0J
 Gatefait, M., 2Y
 Gau, Tsai-Sheng, 3S
 Gaudiello, John, 10, 13
 Geiger, Bob, 3H
 Gergaud, P., 3V
 Ghinovker, Mark, 2J, 3B
 Gin, Peter, 13
 Goddard, Lynford L., 0P, 23
 Gödecke, M. L., 0G
 Godny, Stephane, 07
 Gogolides, Evangelos, 1X
 Gomez, Juan-Manuel, 0T, 0U, 2G, 2K, 2Q, 38
 Gorhad, Kujan, 3D
 Gosali, Benny, 29
 Graves, Trey, 0B
 Gray, Greg, 2J
 Gready, David, 2J, 3B
 Grodzinka, Dominika, 1N
 Gronheid, Roel, 1X, 36
 Grzela, Grzegorz, 1Y
 Guhlemann, Steffen, 1E
 Guillorn, Michael, 10
 Gunay-Demirkol, Anil, 07
 Guo, Wei, 2B, 2E
 Gurevich, Evgeni, 1H
 Gutjahr, Karsten, 1M, 2K
 Gutsch, Manuela, 1V
 Gutsche, Philipp, 39
 Habets, Boris, 1E, 3O
 Hagen, C. W., 0D, 1Z
 Hajaj, Eitan, 2J
 Halder, Sandip, 0O, 0W, 24, 36, 3F
 Halle, Scott, 1K
 Hamieh, Bassem, 1K
 Han, JiWan, 2X
 Han, Sang Hyun, 3B
 Han, Sang-Jun, 1E, 1F, 1L, 2B
 Hand, Sean, 1A
 Hanson, Justin K., 0T
 Hao, Jingan, 2C
 Hao, Xueli, 0T, 2G
 Hartig, Carsten, 12
 Hasan, T., 2Y, 3G
 Haupt, Ronny, 06
 He, Kaiting, 2C
 He, Weiming, 28, 2C
 Hehl, Karl, 04
 Helfenstein, P., 1O
 Henn, M.-A., 0Y
 Heo, Hoyoung, 1F, 25
 Heraud, Stephane, 07
 Hernandez-Charpak, Jorge, 0I
 Herrera, Pedro, 1M
 Herzel, Eitan, 3B
 Higuchi, A., 0L
 Hinnen, P. C., 3G
 Hirano, Ryoichi, 17
 Hodges, Jeffery, 2J
 Hohle, Christoph, 1V
 Hojo, Yutaka, 3K
 Hoogeboom-Pot, Kathleen, 0I
 Horiguchi, Naoto, 1T
 Hossain, Mainul, 0M, 0N
 Hou, Hsin-Ming, 3N
 Hsu, Sharon, 2B, 2E
 Hsu, Y.-B., 3N
 Hu, Dawei, 0Z
 Hu, Haokun, 0Q

Hu, Huayong, 28
 Hu, Jia-Rui, 29, 3S
 Hu, K.-Y., 3G
 Huang, Chi-hao, 3E
 Huang, Chin-Chang, 2R
 Huang, Hao-Lun, 2R
 Huang, Healthy, 2R
 Huang, Jen-Chou, 2R
 Huang, Kun, 3A
 Huang, Vincent, 29
 Humphris, Andrew D. L., 2L
 Hung, Yuting, 2U
 Hunsche, Stefan, 1R, 2O, 3F
 Hussain, Shehzeen, 2G
 Hwang, Chan, 1I, 3B
 Hwang, Jaehee, 1S
 Iddawela, Givantha, 0M
 Ignatova, Velislava, 1Y
 Iida, Susumu, 17
 Ikota, Masami, 14, 16, 1T
 Inoue, Osamu, 0V, 24
 Isbester, Paul, 0M, 1W
 Ito, Y., 0L
 Itzkovich, Tal, 1L, 1M, 2R
 Iwaki, Yuuki, 1T
 Jain, V., 2O
 Jak, M., 2N
 Jang, S.-Y., 3G
 Jau, Jack, 0O, 3F
 Jehoul, Christiane, 2M
 Jeon, Sanghuck, 1F, 25
 Jeon, Se-Ra, 1I
 Jeong, Jong-Mun, 2E
 Ji, Sunkeun, 1J
 Jiang, Lei, 0I
 Jiang, Yuntao, 2C
 Jo, Ahjin, 2P
 Jo, Gyoyeon, 1J
 Jochemsen, Marinus, 1R
 Jones, Chris, 1R
 Ju, JaeWuk, 25, 3O
 Jun, Jinhyuck, 1S
 Jung, Mirim, 1L
 Jung, Sang-Hoon, 2E
 Jung, Woo-Yung, 2O
 Kagalwala, Taher, 1W
 Kamalizadeh, Ferhad, 0T
 Kanakasabapathy, Sivananda, 13
 Kang, Byung Cheol, 0M
 Kang, Hyunwoo, 1J
 Kang, Y.-S., 3G
 Kapteyn, Henry C., 08, 0F, 0I, 0J
 Karl, Robert, Jr., 08, 0F, 0J
 Kasahara, Yusuke, 16
 Kato, Takeshi, 16
 Kawada, Hiroki, 14, 1T
 Ke, Chih-Ming, 29, 3S
 Kea, Marc, 1Y, 2V, 32
 Keller, Nick, 05
 Kent, Eric, 2M

Keyvani, Aliasghar, 18
 Khandelwal, Rahul, 2E
 Kim, Byong, 2P
 Kim, Choidong, 2T
 Kim, Daewoo, 2T
 Kim, Hyeongsoo, 2T
 Kim, Hyun Sik, 32
 Kim, Hyun-Sok, 2E
 Kim, Jungchan, 1J
 Kim, Keunjun, 2T
 Kim, MinGyu, 25, 3O
 Kim, Myoungsoo, 1E, 1F
 Kim, Ryoung-han, 22
 Kim, Sangwoo, 1J
 Kim, Seop, 1E, 3O
 Kim, Shinyoung, 1J, 1S
 Kim, Taeddy, 2E
 Kim, Y.-J., 3G
 Kim, Yangjin, 3L
 Kim, Young Ki, 0T
 Kim, Young-Sik, 1F, 1L, 2B
 King, Sean, 0I
 Klare, Mark, 0M, 0N, 10
 Klein, Dana, 1H
 Klimpel, T., 0C
 Klinov, Michael, 15
 Knobloch, Joshua, 0I
 Koay, Chiew-seng, 1K
 Kobelkov, Sergey, 2X
 Komori, Motofumi, 20
 Konishi, Junko, 16
 Koop, E. J., 3G
 Koshihara, Shunsuke, 0V
 Kramar, John, 11
 Kramer, Geerten, 1B
 Kruijswijk, Stefan, 2B, 2E
 Kruit, P., 1Z
 Kuiper, Stefan, 1B
 Kung, Ji-Fu, 3N
 Kuppuswamy, Vijaya-Kumar Murugesan, 1X
 Kwak, Noh-Jung, 2B
 Kwan, Michael, 0M, 0N
 La Greca, R., 2O
 Labrosse, A., 36
 Laenens, Bart, 0W
 Lamhot, Yuval, 1H
 Lan, Yuan-Ku, 2R
 Larson, Tom, 0M, 0N
 Le Denmat, J. C., 1U
 Le, Fee li, 13
 Lee, Brian, 29
 Lee, Byoung-Ho, 2W, 31
 Lee, Byoung-Hoon, 2B
 Lee, Dohwa, 1L
 Lee, Honggoo, 1E, 1F, 1L
 Lee, Jeongjin, 3B
 Lee, Jongsu, 2B
 Lee, Joonseuk, 1L
 Lee, Ju Suk, 2P
 Lee, JuHan, 25

Lee, Julie, 2D
 Lee, Kangsan, 1L
 Lee, Keibock, 2P
 Lee, Kuntack, 1I, 3B
 Lee, Myungjun, 1L, 26, 2R
 Lee, Seung Yoon, 1I, 3B
 Lee, Shawn, 0T, 0U
 Lee, Sungkoo, 2T
 Lee, Wei Ti, 0M, 0N
 Leewis, Christian, 29
 Le-Gratiet, B., 2O, 2Y
 Lei, Chris, 0Q, 34
 Lei, Ming, 0Q, 27
 Lenahan, Michael, 0M, 0Z, 1W
 Leray, Philippe, 07, 0O, 0W, 24, 2M, 36, 3D, 3F
 Levasier, Leon, 1B
 Levi, Shimon, 15
 Leviant, Tom, 1H
 Levinski, Vladimir, 1L
 Levy, Ady, 1L, 26, 2R
 Lewis, Brian, 1Y
 L'herron, Benoit, 13
 Li, Chen, 2V
 Liao, C. H., 29
 Liebig, Thomas, 1B
 Likhachev, Dmitry, 12
 Lin, Bill, 2U
 Lin, Hua-Tai, 3S
 Lin, Peter, 3Q
 Lin, Yi-Shih, 2C
 Lindenfeld, Ze'ev, 1H, 2J
 Lio, En Chuan, 2U
 Liu, Chang, 2C
 Liu, Kevin, 0O, 3F
 Liu, Shiyuan, 23
 Liu, Zephyr, 1L
 Lokhorst, S. R., 0D, 1Z
 Lopez-Rios, Raymond, 0F
 Lorusso, Gian Francesco, 0V, 1T, 24
 Loubet, Nicolas, 10
 Luijten, Carlo, 29
 Lund, Parker, 10
 Lung, Hsien-Yen, 2R
 Luo, Woel-Bin, 3S
 Ma, Won-Kwang, 2B
 Mack, Chris A., 0A, 1Q
 Mahendrakar, Sridhar, 0M, 0Z, 1W
 Mahoney, Mark O., 0T
 Mailfert, Julien, 0W
 Mancini, Giulia F., 0F, 0J
 Mancuso, Christopher, 08
 Manka, James, 1H
 Marciano, Tal, 1H, 1M
 Maret, M., 3V
 Martin, N., 1U
 Maruyama, Kotaro, 1J, 3N
 Massier, Jennifer, 1N
 Matsuki, Kazuto, 20
 Mcardle, Timothy, 0N
 McGarvey, Steve, 3J
 McGowan, Richard, 1M
 Mc Namara, Elliott, 1I
 Megens, Henry, 1Y
 Melnikov, Andrey, 3X
 Menchtchikov, Boris, 2M
 Mendoza, Brock, 13
 Miceli, Giacomo, 2B, 2E
 Mileham, Jeffrey, 2W, 31
 Miller, Andrei, 3I
 Miller, Eric, 13
 Milligan, Eric, 1A
 Minghetti, Blandine, 0U
 Mish, Barbara, 3C
 Mitsubishi, Mamoru, 3L
 Mohacsi, I., 1O
 Mokaberi, Babak, 2V, 32
 Moore, Sam, 2J
 Morey, Philippe, 3M
 Mos, Evert, 1Y
 Muckenhirn, Sylvain, 0R
 Mulkens, Jan, 1Y
 Murnane, Margaret M., 08, 0F, 0I, 0J
 Muthinti, Raja, 10, 13
 Nabeth, Jeremy, 1F, 25
 Nardi, Damiano, 0I
 Ndiaye, O., 1U
 Nelson, Florence, 13
 Newell, Travis, 3I
 Ngo, Desmond, 29
 Nguyen, Hoang, 3Q
 Nooitgedagt, T., 2N
 Noot, Marc, 1I, 29, 2V
 Noyes, Ben F., III, 2V, 32
 Oh, Jong Hun, 32
 Oh, Nang-Lyeom, 1I, 1S
 Oh, SeungHwa, 1I
 Oh, Soonho, 3B
 Ohashi, Takeyoshi, 0V
 Ohya, Kaoru, 17
 Okagawa, Yutaka, 24
 Omote, K., 0L
 O'Mullane, Samuel, 05
 Onishi, Tsuyoshi, 14
 Osborne, Jason, 1A
 Osten, W., 0G
 Ott, John, 10
 Overtoom, Ton, 1B
 Owen, David M., 2W, 31
 Palande, Ashwin, 2V
 Pan, Yan, 3Q
 Pandev, Stilian, 06
 Panteleit, Friedhelm, 1V
 Park, Byungjun, 1J
 Park, Chanha, 1J, 1S
 Park, Chris, 1S
 Park, Dong-Gyu, 2E
 Park, Dongsuk, 1M, 2K
 Park, Jeongsu, 2T
 Park, Kevin, 2V
 Park, Minwoo, 1J

Park, Noh-Kyoung, 1I
 Park, S.-J., 3G
 Park, Sang-il, 2P
 Park, Sean, 1S
 Pathangi, Hari, 1X
 Pearl, Haim, 3I
 Pelletier, A., 1U
 Peng, Yi-Hsing, 0W
 Peterhänsel, S., 0G
 Pierson, Bill, 1F, 25, 2K
 Pitney, John A., 3X
 Planchot, J., 1U
 Pois, Heath, 0M, 0N
 Pomplun, Jan, 39
 Porter, Christina L., 08, 0F, 0J
 Prentice, C., 2O, 2Y
 Pret, Alessandro Vaglio, 1X
 Qiu, Jian, 3C
 Raghunathan, Ananthan, 1Q
 Raghunathan, Sudhar, 2M
 Rajasekharan, Bijoy, 1Y
 Rajendran, R., 1O
 Ramanathan, Vidya, 06, 1M
 Rebel, Gerard, 1N
 Reich, Elke, 1V
 Reichenadter, Jonathan, 0F
 Ren, Zhou, 0Z
 Rey, S., 3V
 Rider, Gavin C., 2S
 Rijnbeek, Ramon, 1B
 Rio, David, 0W
 Robert, F., 1U
 Robertson, Stewart, 0B
 Robinson, John C., 1F, 25, 2K
 Roelofs, Christian, 3D
 Röbiger, Martin, 1E
 Röth, Klaus-Dieter, 3M
 Rudolph, Matthias, 1V
 Sadeghian, Hamed, 0H, 18, 2Z
 Sakai, Hideo, 14
 Saltoun, Lilach, 1H
 Samudrala, Pavan, 0T, 0U, 2G, 2K, 2Q, 38
 Sanko, Dmitry, 06
 Sato, Hironobu, 16
 Saulnier, Nicole, 22
 Saxena, Shweta, 0Z
 Schmidt, Frank, 39
 Schmitt-Weaver, Emil, 1Y
 Schoonewelle, Hielke, 2M
 Seaberg, Matthew H., 08
 Seino, Yuriko, 16
 Seipp, Steven, 0Z
 Sella, Noga, 1H
 Sendelbach, Matthew, 0M, 10, 13
 Seo, Moo-Young, 2E
 Shanblatt, Elisabeth R., 08, 0F, 0J
 Sharoni, Ofir, 3D
 Shi, Xuelong, 2C
 Shi, Yaoming, 3A
 Shi, Yating, 23
 Shifrin, Michael, 1W
 Shinoda, Shinichi, 3K
 Shirasaki, Hirokimi, 21
 Sieg, Stuart, 13, 1K
 Silver, R. M., 0Y
 Simiz, J.-G., 2O
 Sindo, Hiroyuki, 3K
 Singh, Amarnauth, 3C
 Singh, A., 36
 Smith, Mark D., 0B, 1L, 26, 2R
 Smith, Martin, 3C
 Snow, Patrick, 1M, 2K
 Socha, Robert, 2M
 Sohn, M. Y., 0Y
 Song, Da, 0Z
 Song, Ho Young, 34, 3Q
 Song, Jinyan, 2R
 Song, Yi, 2B, 2E
 Song, Zhiyang, 2A
 Staals, Frank, 29
 Steidel, Katja, 1V
 Steinert, Steffen, 3D
 Storms, Greet, 1I
 Sturtevant, John, 1Q
 Su, Xiaojing, 2A
 Subrahmanyam, Pradeep, 26
 Subramanian, Ganesh, 0N
 Subramany, Lokesh, 0U, 2G, 2K, 2Q, 38
 Sugahara, Hitoshi, 3K
 Sugita, Naohiko, 3L
 Sun, Che-Yuan, 3S
 Sun, Kyu-Tae, 1S, 2B, 2E
 Sun, Lei, 22
 Sung, Jun Ha, 32
 Szucs, A., 1U
 Takahashi, Satoru, 1T
 Takamasu, Kiyoshi, 1T
 Tamer, Mehmet S., 18
 Tanaka, Yasushi, 2W
 Tang, Hao, 22
 Tanksalvala, Michael, 0F, 0J
 Tarshish-Shapir, Inna, 2J, 3B
 Taylor, Patrick A., 2P
 Theeuwes, Thomas, 2B, 2E
 Thrun, Xaver, 1V
 Tian, Qing, 0Q, 27, 34
 Tian, Ye, 0T
 Tijssen, Robin, 29
 Tillotson, Brock, 3I
 Timoney, Pdraig, 0M, 1A
 Timoshkov, Vadim, 1R
 Tinnemans, Patrick, 2M
 Tiron, Raluca, 15
 Tomimatsu, Satoshi, 14
 Tomlinson, Derek, 0Q
 Tondare, V. N., 09
 Torikawa, Shota, 14
 Toyoda, Yasutaka, 3K
 Toyoshima, Yuya, 3N
 Trautzsch, Thomas, 3D

Tripp, Marie, 0I	Weng, Tang Chun, 2U
Tritchkov, Alexander, 2X	Wildenberg, Jochem, 1Y
Triyoso, Dina, 0N	Willems, Lotte, 1Y
Tsai, Frankie, 29	Wise, Rich, 2M
Tsai, Hsueh-Jen, 2R	Wisse, Baukje, 2B, 2E
Tsuda, Hirotaka, 20	Witvoet, Gert, 1B
Tu, Ward, 29	Wolfling, Shay, 07, 10, 13
Tuffy, Paul, 1S, 2M	Wormington, Matthew, 13
Tung, Yu-Lung, 3S	Wu, Kevin, 0Q, 27, 34
Turovets, Igor, 07	Wu, Qiang, 2C
Unal, N., 0C	Wu, Sarah, 2J
Urbanowicz, Adam M., 12	Xiao, Lihong, 2C
Urenski, Ronen, 07	Xie, Qian, 2D
v. d. Laan, H., 2N	Xing, Bin, 2C
v. d. Zouw, G., 2N	Xu, Yiping, 3A
Vaglio Pret, Alessandro, 0B, 1X	Xu, Yongan, 22
Vaid, Alok, 06, 0M, 0N, 0Z, 1A, 1W	Yamaguchi, Satoru, 16
Valley, John F., 3X	Yamazaki, Y., 3N
van de Mast, Frank, 1I	Yang, Elvis, 3E
van der Donck, Jacques, 35	Yang, Hyunjo, 1J, 1S
van der Walle, Peter, 35	Yang, Jui-Chin, 2R
van Dijsseldonk, Anton, 1B	Yang, Mars, 3E
van Es, Maarten H., 18, 2Z	Yang, T. H., 3E
van Haren, Richard, 3D	Yap, Lipkong, 2K
van Heijst, Joost, 1I, 1Y	Yathapu, Nithin, 3J
van Keulen, Fred, 0H	Yaziv, Tal, 1H
Van Veen, Martijn, 29	Ye, Lei, 28
van Zwet, Erwin, 1B	Yellai, Naren, 0M, 1W
Vanoppen, P., 2N	Yoo, Young-kook, 2P
Varanasi, Rao, 3C	Yoon, Nam Hee, 0Z
Venkatachalam, Panneerselvam, 2D	Young, Stuart, 29
Venkataraman, Kartik, 06, 0Z	Yu, Chun Chi, 2U
Verduijn, Erik, 22	Zafar, Khurram, 2D, 3Q
Verduin, T., 0D, 1Z	Zandiatashbar, Ardavan, 2P
Vergaaj-Huizer, Lydia, 1Y	Zeidler, Dirk, 1V
Verma, Alok, 2B, 2E	Zeng, Xuefeng, 34, 3Q
Verstappen, Leon, 1Y	Zhan, Yunkun, 3A
Villarrubia, J. S., 09	Zhang, Bosheng, 08
Vladár, A. E., 09	Zhang, Kedi, 0P
Volatier, Jean-Baptiste, 35	Zhang, Pengcheng, 0O, 3F
Voncken, M. M. A. J., 3G	Zhang, Qiang, 2C
Wagner, Mark, 1H	Zhang, Rui, 2B, 2E
Wahl, Jeremy, 0N	Zhang, Xiaoxiao, 06, 1A
Wan, Alex, 3F	Zhang, Youping, 1S
Wang, Fei, 0O, 3F	Zhang, Zhensheng, 3A
Wang, Gary Ch., 2U	Zhao, Bin, 2L
Wang, I-Lin, 2R	Zhao, Yan, 0Q, 27, 34
Wang, Lester, 3F	Zheng, Chumeng, 1K
Wang, Liuchen, 34	Zhivotovsky, Alexander, 3J
Wang, Sybil, 2U	Zhou, H., 0Y
Wang, Wenhui, 22	Zhou, Jianming, 2J
Wang, Xiaozhen, 0P	Zhou, Xinjian, 1R
Wang, Ying, 0N	Zhou, Yue, 1M
Wardenier, Peter, 1Y	Zhu, Jinlong, 0P, 23
Warrick, Scott, 0X	Zimmermann, Y., 36
Watanabe, Hidehiro, 17	Zschiedrich, Lin, 39
Wei, Yayi, 2A	Zuniga, Christian, 1Q
Weinberg, Yakov, 15	
Weintraub, Jeffrey, 0X	
Welch, Steven, 2B, 2E	

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Opening Remarks and Award Announcement

Martha I. Sanchez, IBM Research - Almaden (United States)

1 Keynote Session

Martha I. Sanchez, IBM Research - Almaden (United States)

Vladimir A. Ukraintsev, Qorvo™ (United States)

2 Optical Metrology I

Daniel J. C. Herr, The University of North Carolina at Greensboro (United States)

Richard M. Silver, National Institute of Standards and Technology (United States)

3 SEM I: Modeling and Simulation

Benjamin D. Bunday, SUNY Poly SEMATECH (United States)

Shunsuke Koshihara, Hitachi High-Technologies Corp. (Japan)

4 New Horizons

Richard M. Silver, National Institute of Standards and Technology (United States)

Daniel J. C. Herr, The University of North Carolina at Greensboro (United States)

5 X-ray Methods

John A. Allgair, Nanometrics Inc. (United States)

Shunsuke Koshihara, Hitachi High-Technologies Corp. (Japan)

6 Inspection

Timothy F. Crimmins, Intel Corp. (United States)

Matthew J. Sendelbach, Nova Measuring Instruments Inc. (United States)

7 Process Control

Alok Vaid, GLOBALFOUNDRIES Inc. (United States)

Alek C. Chen, ASML (United States)

8 Optical Metrology II

Matthew J. Sendelbach, Nova Measuring Instruments Inc. (United States)

Alek C. Chen, ASML (United States)

9 SEM II

Ofer Adan, Applied Materials, Ltd. (Israel)

Timothy F. Crimmins, Intel Corp. (United States)

- 10 AFM
Vladimir A. Ukraintsev, Qorvo™ (United States)
- 11 Overlay: Metrology Target Design and Optimization
Alexander Starikov, I&I Consulting (United States)
Byoung-Ho Lee, Ultratech, Inc. (United States)
- 12 Overlay Optimization: Joint Session with Conferences 9778 and 9780
John C. Robinson, KLA-Tencor Corp. (United States)
Young Seog Kang, SAMSUNG Electronics Co., Ltd.
(Korea, Republic of)
- 13 Mask Inspection
Alek C. Chen, ASML (United States)
Byoung-Ho Lee, Ultratech (United States)
- 14 Design Interaction with Metrology: Joint Session with Conferences
9778 and 9781
Alexander Starikov, I&I Consulting (United States)
Jason P. Cain, Advanced Micro Devices, Inc. (United States)
- 15 Late Breaking News
Martha I. Sanchez, IBM Research - Almaden (United States)
Alok Vaid, GLOBALFOUNDRIES Inc. (United States)

Introduction

The 30th conference on Metrology, Inspection, and Process Control for Microlithography had close to a record number of submitted abstracts. The Program Committee Members, as a result, put much time and effort in producing a high quality program of technical content for the audience.

The conference began with two outstanding Keynote presentations. Martin van den Brink from ASML started the Keynote session with "Holistic Lithography and Metrology's Importance in Driving Patterning Fidelity", laying out today's metrology developments in a 30 year context. This was followed by Markus Kuhn from Intel with "Smart Metrology for Continuing Moore's Law Scaling", describing the need for analytical laboratories to step in to supplement manufacturing metrology.

To celebrate the 30th meeting of the conference, champagne and hors d'oeuvres were served as the conference attendees played a game to test their knowledge of metrology over the last 30 years.

A strong contingent of student papers made it difficult for the judges to award the Best Student paper this year. Their presentations were professional and the content was high quality. Obvious effort to improve SEM modeling and to use it for OPC and even for in-line measurements were prominent. There were an overwhelming number of overlay metrology papers underpinning the field's importance, improvement in accuracy, and paving the way to a nm uncertainty. There has been good progress on X-ray CD metrology (including in-line metrology), along with progress in e-beam and optical inspection of defects with dimensions below 100 nm.

Joint sessions continued to be an excellent way to merge and interact with other conferences. This year we had two joint sessions.

SESSION 12: Overlay Optimization: The first joint session, with the Optical Microlithography conference 9780 and 9778 chaired by John C. Robinson and Young Seog Kang, benefitted from the strong number of overlay abstracts submitted this year:

- "Patterned wafer geometry (PWG) metrology for improving process-induced overlay and focus problems," (*Invited Paper*) Timothy A. Brunner, *et al.*, GLOBALFOUNDRIES Inc. [9780-31]
- "Root cause analysis of overlay metrology excursions with scatterometry overlay technology (SCOL)," Vidya Ramanathan, KLA-Tencor New York; *et al.* [9778-117]
- "Assessments of image-based and scatterometry-based overlay targets," Chiew-Seng Koay, *et al.*, IBM Corp. [9778-55]
- "Lithography-aware overlay metrology target design method," Myungjun Lee, *et al.*, KLA-Tencor Corp. [9778-56]

- "Improvement of unbalanced illumination induced telecentricity within the exposure slit," Jong Hoon Jang, *et al.*, SAMSUNG Electronics Co., Ltd. [9780-32]

SESSION 14: Design Interaction with Metrology: The second joint session was with the conference on Design-Process-Technology Co-optimization for Manufacturability 9781 and 9778 chaired by Alexander Starikov and Jason P. Cain—was standing-room only:

- "Modeling metrology for calibration of OPC models," Chris A. Mack, *et al.*, Lithoguru.com [9778-61]
- "OPC optimization techniques for enabling the reduction of mismatch between overlay metrology and the device pattern cell," Shinyoung Kim, *et al.*, SK Hynix, Inc. [9778-137]
- "The innovative PWQ method for accurate weak point extraction in DRAM," Daehan Han, *et al.*, SAMSUNG Electronics Co., Ltd. [9781-27]
- "Process window limiting hot spot monitoring for high-volume manufacturing," Marinus Jochemsen, *et al.*, ASML [9778-63]

Continued below are the winners of the 2015 Diana Nyysönen Memorial award for best paper and the 2016 Karel Urbanek Best Student paper award.

Martha I. Sanchez
Vladimir A. Ukraintsev

The Diana Nyyssonen Memorial Award for Best Paper

Diana Nyyssonen was a pioneer in the field of dimensional metrology. Her early interests in optics were formed under the tutelage of Professor Edward L. O'Neill at Boston University. In 1965 she went to work for Brian J. Thompson and George B. Parrent, Jr. at Technical Operations, Inc., Burlington, Massachusetts. Diana's knowledge of physical optics and related modeling grew rapidly as she worked on the teams developing the theory of partially coherent imaging, physical models, equipment and applications for the US government, astronomy, and industry. Her professional circle at that time included George O. Reynolds, John B. DeVelis, Adriaan Walthier, Philip S. Considine, Richard J. Becherer, and Richard E. Swing.

In 1969 Diana Nyyssonen joined the Image Optics and Photography Section of the Metrology Division at the National Bureau of Standards (NBS), initially working for Calvin S. McCamy on microdensitometry, then on linewidth measurements for integrated circuit manufacturing applications.

Sponsored by NBS, Diana also attended the Institute of Optics, University of Rochester at Rochester, New York where Professor B. J. Thompson, Director of the Institute, was her advisor. She completed her PhD in 1975 with her thesis "High resolution microdensitometry of photographic emulsions" reflecting on the scientific foundations and the outlook of the things to come. Dr. Nyyssonen's modeling of thin films observed by an optical microscope demonstrated that line (space) width smaller than Rayleigh resolution limit can be measured. She produced linewidth measurements in photomasks with calibration based on physical modeling and first principles, establishing the first critical dimension standards for the microelectronics industry and the foundation of today's dimensional metrology.

Dr. Diana Nyyssonen; 1980

(Image courtesy Jeffrey Nyyssonen Swing)

Dr. Nyyssonen left NBS in 1985 to form her own metrology company, and then joined IBM at East Fishkill, New York in 1988. Continuing the development of accurate optical modeling of imaging of thick films with Christopher P. Kirk, NBS, and other teams, she started projects on metrology with scatterometry and interference microscopy, modeled imaging in low voltage CD-SEM, and spearheaded the establishment of CD-AFM.

Diana Nyyssonen's personal contributions to the field of dimensional metrology, as well as her collaborations and mentorships in the industry, consortia, and academia, accelerated and influenced the development of basic technology and metrology applications with optical microscopy and scatterometry, SEM, and AFM.

Metrology, Inspection, and Process Control for Microlithography is the leading international forum for the discussion and presentation of technical advances in the broader field of semiconductor metrology. The Diana Nyyssonen Memorial Award for the Best Paper at this Conference recognizes the most significant current contributions.

Due to the Conference's long history, significant attendance, and high paper counts, to win this Award requires a very significant new contribution to the field. The selection of the best paper is initiated during the Conference by nomination, followed by extensive review by the Program Committee. It is based on both the technical merit and persuasiveness of the oral presentation and the overall quality of the published paper. Past award winners include leading international researchers in the area of semiconductor metrology and process control, whose contributions have fundamentally improved the way semiconductors are manufactured.

We are pleased to honor the winners of the Diana Nyyssonen Memorial Award for the Best Paper of 2015, as well as those who have won in previous years:

2015

Narender Rana, Yunlin Zhang, Donald Wall, Bachir Dirahoui, and Todd C. Bailey, "Machine Learning and Predictive Data Analytics Enabling Metrology and Process Control in IC," Proc. SPIE vol. 9424, 94241I (2015).

2014

András E. Vladár, John S. Villarrubia, Jasmeet Chawla, Bin Ming, Joseph R. Kline, Scott List, Michael T. Postek, "10 nm three-dimensional CD-SEM metrology," Proc. SPIE vol. 9050, 90500A (2014).

2013

Ozan Ugurlu, Michael Strauss, Gavin Dutrow, Jeff Blackwood, Brian Routh, Corey Senowitz, Paul Plachinda, Roger Alvis, "High-volume process monitoring of FEOL 22nm FinFET structures using an automated STEM," Proc. SPIE vol. 8681, 868107 (2013).

2012

Narender Rana and Dario Goldfarb, "Bridging CD metrology gaps of advanced patterning with assistance of nanomolding," Proc. SPIE, Vol. 8324, 83241M (2012).

2011

Shiano Ono, Miyuki Yamane, Mitsuo Ogasawara, Akira Katakami, Jiro Yugami, Masanari Koguchi, Hiroyuki Shinada, Hiroshi Kakibayashi, Kazuto Ikeda, and Yuzuru Ohji, "Highprecision edge-roughness measurement of transistor gates using three-dimensional electron microscopy combined with marker-assisted image alignment," Proc. SPIE, Vol. 7971, 79710M (2011).

2010

David Laidler, Koen D'havé, Anne-Laure Charley, Philippe Leray, Shaunee Cheng, Mircea Dusa, Peter Vanoppen, and Paul Hinnen, "A single metrology tool solution for complete exposure tool setup," Proc. SPIE, Vol. 7638, 763809 (2010).

2009

Benjamin Bunday, Aaron Cordes, John Allgair, Vasiliki Tileli, Yohanan Avitan, Ram Peltinov, Maayan Bar-zvi, Ofer Adan, Eric Cottrell, and Sean Hand, "Phenomenology of electron-beam-induced photoresist shrinkage trends," Proc. SPIE, Vol. 7272, 72721B (2009).

2008

Alok Vaid, Rohit Pal, Matthew Sendelbach, Shahin Zangoie, Kevin Lensing, and Carsten Hartig, "Scatterometry as technology enabler for embedded SiGe process," Proc. SPIE, Vol. 6922, 69220U (2008).

2007

Matthew Sendelbach, Javier Ayala, and Pedro Herrera, "Predicting electrical measurements by applying scatterometry to complex spacer structures," Proc. SPIE, Vol. 6518, 651825 (2007).

2006

Masafumi Asano, Takahiro Ikeda, Toru Koike, and Hideaki Abe, "In-line CD metrology with combined use of scatterometry and CD-SEM," Proc. SPIE, Vol. 6152, 61521V (2006).

2005

John S. Villarrubia and Benjamin D. Bunday, "Unbiased estimation of linewidth roughness," Proc. SPIE, Vol. 5752, 480 (2005). Xxii

2004

Christopher P. Ausschnitt, "A new approach to pattern metrology," Proc. SPIE, Vol. 5375, 51 (2004).

2003

John S. Villarrubia, Andras E. Vladar, and Michael T. Postek, "Simulation study of repeatability and bias in the CD-SEM," Proc. SPIE, Vol. 5038, 138 (2003).

2002

Jon L. Opsal, Hanyou Chu, Youxian Wen, Yia-Chung Chang, and Guangwei Li, "Fundamental solutions for real-time optical CD metrology," Proc. SPIE, Vol. 4689, 163 (2002).

2001

Sylvain Muckenhirn, A. Meyyappan, Kelvin Walch, Mark J. Maslow, Geert Vandenberghe and Johannes van Wingerden, "SPM characterization of anomalies in phase-shift mask and their effect on wafer features," Proc. SPIE, Vol. 4344, 188 (2001).

The Karel Urbánek Best Student Paper Award

Karel Urbánek studied electronics and high-vacuum physics at the Charles University in Prague, the valedictorian of his class. To earn his way through college, and to learn about the life in the West, he worked as a tour guide. That is how he met two key people in his life and career: Lida Náprstek, then a student at Radcliffe College leading a group of American school kids, and Sonny (Melville) Marx, an investment banker from San Francisco. After graduation he used this learning and cash to escape the soviet system by flying to a “vacation” in Cuba. He slipped away during a stopover in Halifax, Nova Scotia. His first call was to Lida; the second was to Sonny. He requested asylum. The local American consul arranged for his entry into the United States.

Karel Urbánek

(Image courtesy Lida Urbanek)

Karel soon found a job with the Lincoln Laboratory in Cambridge, Massachusetts, then moved to the San Francisco Bay Area. He joined Varian Associates and worked for Bill Wheeler on vacuum equipment for semiconductor manufacturing.

Recognizing an opportunity in the new field of sputtering for thin film deposition, Karel and fellow Varian employees John Schwabacher, Ed Kerswill, Al Lang, and Barry Hart founded Randex in 1970.

By 1973, with Randex business in rapid growth, its founders agreed to an acquisition by Perkin-Elmer. Karel became the research director for the Ultek division of Perkin-Elmer in Palo Alto, California.

Sputtering projects often led to the need to accurately measure the thickness of the deposited film. Recognizing another opportunity, some of the original Randex team (Urbánek, Schwabacher, Kren, Hart, and Kerswill) formed Tencor in 1976. Bill Wheeler and Jerry Gabe later joined Tencor. Sonny Marx, their venture capitalist in the Randex start up, insisted that they re-invest their gains in this new venture, a move to leverage their past success and to control their new business, ultimately making most of them wealthy.

Tencor's first product was the Alpha-Step profilometer in 1977. It used a simple but very robust method for measuring displacement. Urbánek even insisted on literally kicking a packing case containing an Alpha-Step across a room, then opening it up to set up and, within minutes, measure film thickness and step height. Simple to use, stable and repeatable to sub-1nm the tool was an instant success. The Tencor team then bet the company on their next big product: Surfscan wafer inspection tool. They nearly

bankrupted the company developing reliable detection of small defects and automation. That pioneering technology, as in the Alpha-Step, also quickly became ubiquitous and it is still in use today.

Karel Urbánek served as CEO and Chairman of the Board of Tencor for fifteen years until his death in 1991. He was also active in the SEMI International Standards Program and was honored in 1992 with the creation of the Karel Urbánek Award, the most prestigious honor for participants in the SEMI International Standards Program.

Karel and Lida Urbánek were passionate supporters of education, particularly in science and engineering. This support lives on through the Karel Urbánek Fellowship at Stanford University, the Karel Urbánek Laboratories at the Charles University in Prague, and the Urbánek /Levy Education Fund for the children of KLA-Tencor employees.

The Karel Urbánek Best Student Paper Award sponsored by KLA-Tencor Corp. was created in 2014 to recognize the best paper authored by a current student at the conference. In order to be eligible, the student must be the primary author and must present the work at the conference. It is our great pleasure to recognize this year's winner along with previous recipients:

2016

Maria Laura Gödecke, Sandy Peterhänsel, Karsten Frenner, and Wolfgang Osten, "Measurement of asymmetric side wall angles by coherent scanning Fourier scatterometry," [9778-16]

2015

Kathleen M. Hoogeboom-Pot, Jorge N. Hernandez-Charpak, Travis Frazer, Xiaokun Gu, Emrah Turgut, Erik H. Anderson, Weilun L. Chao, Justin M. Shaw, Ronggui Yang, Margaret M. Murnane, Henry C. Kapteyn, Damiano Nardi, "Mechanical and thermal properties of nanomaterials at sub-50nm dimensions characterized using coherent EUV beams," [9424-43]

2014

Thomas Verduin, Cornelis W. Hagen, Pieter Kruit, "Determination of line edge roughness in low dose top-down scanning electron microscopy images," Proceedings of SPIE Vol. 9050, 90500L (2014).